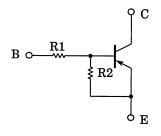
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

RN2114FV,RN2115FV,RN2116FV RN2117FV,RN2118FV

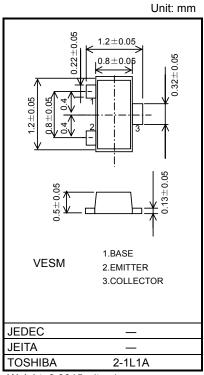
Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications

- Built-in bias resistors
- Simplified circuit design
- Reduced quantity of parts and manufacturing process
- Complementary to RN2114FV~RN2118FV

Equivalent Circuit and Bias Resistor Values



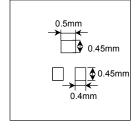
Type No.	R1 (kΩ)	R2 (kΩ)
RN2114FV	1	10
RN2115FV	2.2	10
RN2116FV	4.7	10
RN2117FV	10	4.7
RN2118FV	47	10



Weight: 0.0015g (typ.)

Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Collector-base voltage	RN2114FV~2118FV	V _{CBO}	-50	V	
Collector-emitter voltage	KN2114FV-2110FV	V _{CEO}	-50	V	
	RN2114FV		-5		
Emitter-base voltage	RN2115FV		-6	V	
	RN2116FV	V _{EBO}	-7		
	RN2117FV		-15		
	RN2118FV		-25		
Collector current		IC	-100	mA	
Collector power dissipation	RN2114FV~2118FV	P _C (Note)	150	mW	
Junction temperature	KINZ114FV~2110FV	Tj	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



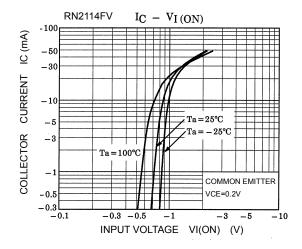
Note: Mounted on FR4 board (25.4 mm × 25.4 mm × 1.6mmt)

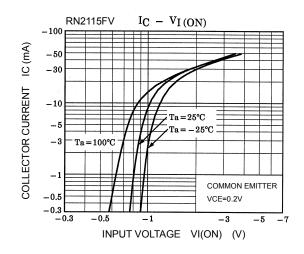


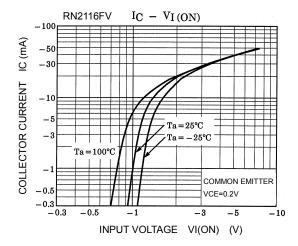
Electrical Characteristics (Ta = 25°C)

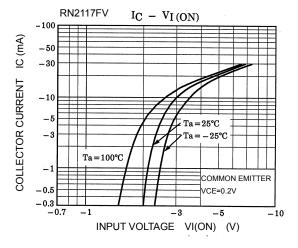
Chara	acteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	DN9444EV9449EV	I _{CBO}	_	$V_{CB} = -50V, I_E = 0$	_	_	-100	nA
	RN2114FV~2118FV			V _{CE} = -50V, I _B = 0	_	_	-500	
	RN2114FV	I _{EBO}	_	$V_{EB} = -5V, I_{C} = 0$	-0.35	_	-0.65	mA
	RN2115FV			$V_{EB} = -6V, I_C = 0$	-0.37	_	-0.71	
Emitter cut-off current	RN2116FV			$V_{EB} = -7V, I_C = 0$	-0.36	_	-0.68	
	RN2117FV			V _{EB} = -15V, I _C = 0	-0.78	_	-1.46	
	RN2118FV			V _{EB} = -25V, I _C = 0	-0.33	_	-0.63	
DC surrent sein	RN2114FV~16FV,18FV			V _{CE} = -5V,	50	_	_	
DC current gain	RN2117FV	h _{FE}	_	I _C = -10mA	30	_	_]]
Collector-emitter saturation voltage	RN2114FV~2118FV	V _{CE} (sat)	_	I _C = -5mA, I _B = -0.25mA	_	-0.1	-0.3	V
	RN2114FV				-0.5	_	-2.0	V
	RN2115FV				-0.6	_	-2.5	
Input voltage (ON)	RN2116FV	V _{I (ON)}	_	$V_{CE} = -0.2V,$ $I_{C} = -5mA$	-0.7	_	-2.5	
	RN2117FV				-1.5	_	-3.5	
	RN2118FV				-2.5	_	-10.0	
	RN2114FV	V _I (OFF)		V _{CE} = -5V, I _C = -0.1mA	-0.3	_	-0.9	V
Input voltage (OFF)	RN2115FV		_		-0.3	_	-1.0	
	RN2116FV				-0.3	_	-1.1	
	RN2117FV				-0.3	_	-3.0	
	RN2118FV				-0.5	_	-5.7	
Transition frequency	RN2114FV~2118FV	f _T	_	V _{CE} = -10V, I _C = -5mA	_	200	_	MHz
Collector output capacitance	RN2114FV~2118FV	C _{ob}	_	V _{CB} = -10V, I _E = 0, f = 1MHz	_	3.0	_	pF
	RN2114FV	R1	_	_	0.7	1.0	1.3	-
	RN2115FV				1.54	2.2	2.86	
Input resistor	RN2116FV				3.29	4.7	6.11	kΩ
	RN2117FV				7	10	13	1
	RN2118FV				32.9	47	61.1	
Resistor ratio	RN2114FV	R1/R2	_	_	_	0.1	_	
	RN2115FV				_	0.22	_]
	RN2116FV				_	0.47	_]
	RN2117FV				_	2.13	_	1
	RN2118FV					4.7	_	1

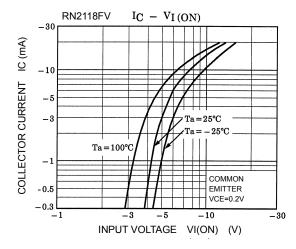
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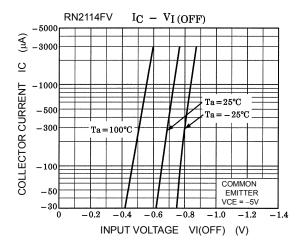


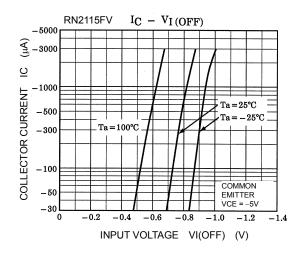


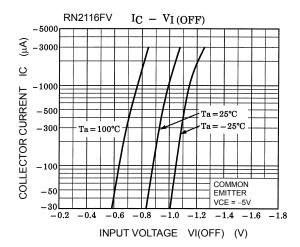


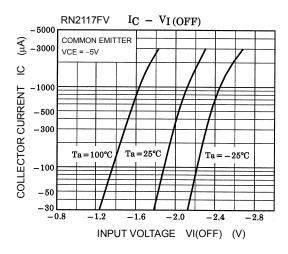


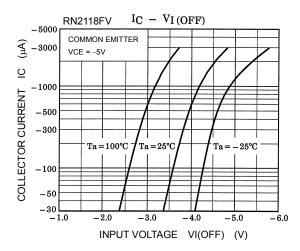
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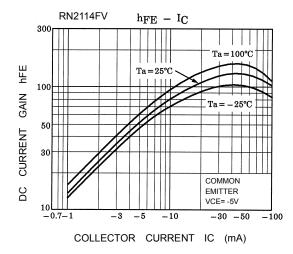


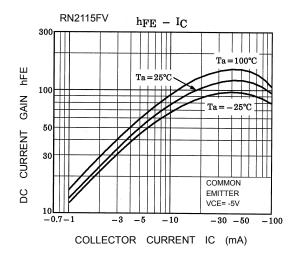


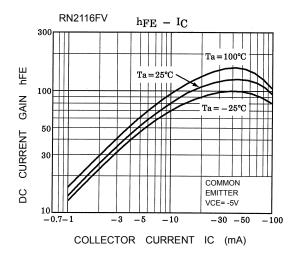


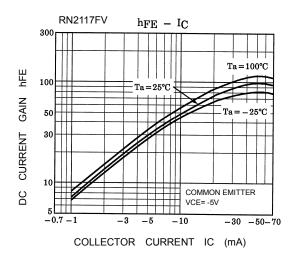


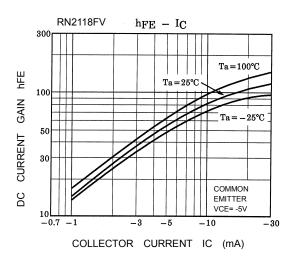




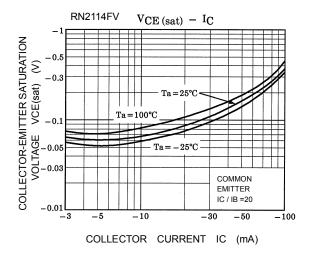


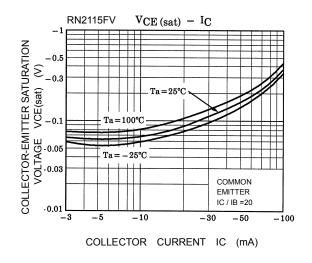


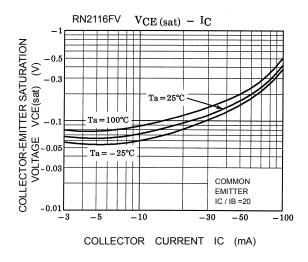


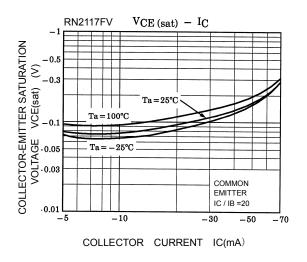


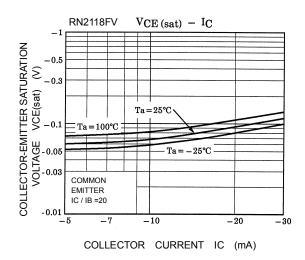
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Type Name	Marking
RN2114FV	Type Name YQ
RN2115FV	Type Name YS
RN2116FV	Type Name YT
RN2117FV	Type Name
RN2118FV	Type Name YW

7

RESTRICTIONS ON PRODUCT USE

Handbook" etc..

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